

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI ULBM2T** is Designed for Class C, FM Land Mobile Applications up to 470 MHz.

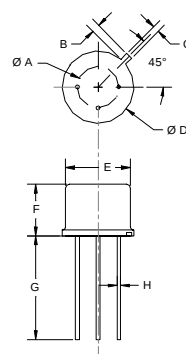
FEATURES:

- Common Emitter
- $P_G = 6.0$ dB at 2.0 W/470 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	0.75 A
V_{CB0}	36 V
V_{CEO}	16 V
V_{CES}	36 V
V_{EBO}	4.0 V
P_{DISS}	5 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	35 $^\circ\text{C/W}$

PACKAGE STYLE TO-39



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A		.200 / 5.080
B	.029 / 0.740	.045 / 1.140
C	.028 / 0.720	.034 / 0.860
D	.335 / 8.510	.370 / 9.370
E	.305 / 7.750	.335 / 8.500
F	.240 / 6.100	.260 / 6.600
G		.500 / 12.700
H	.016 / 0.407	.020 / 0.508

ORDER CODE: ASI10676

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 25$ mA	16			V
BV_{CES}	$I_C = 5.0$ mA	36			V
BV_{EBO}	$I_E = 1.0$ mA	4.0			V
I_{CBO}	$V_{CE} = 15$ V			1.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 100$ mA	20			---
C_{ob}	$V_{CB} = 12$ V $f = 1.0$ MHz			10	pF
P_G η_c	$V_{CC} = 12.5$ V $P_{OUT} = 2.0$ W $f = 470$ MHz	6.0	55		dB %